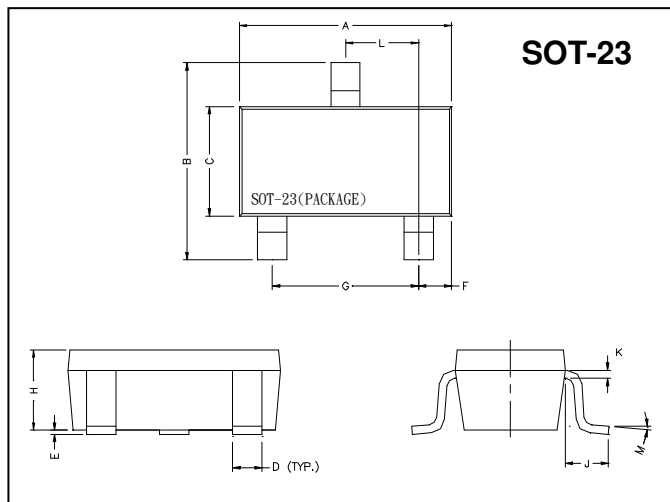
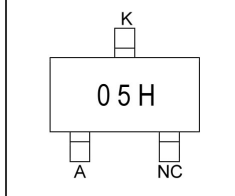


G401SD**SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 30V, CURRENT 0.2A****Description**

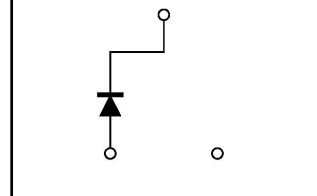
The G401SD is high frequency rectification for switching power supply.

Package Dimensions

Marking :



Circuit :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at TA = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+125	°C
Storage Temperature	T _{stg}	-55 ~ +125	°C
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	30	V
Maximum RMS Voltage	V _{RMS}	21	V
Maximum DC Blocking Voltage	V _{DC}	30	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	3.0	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	40	pF
Maximum Average Forward Rectified Current	I _o	0.2	A
Total Power Dissipation	PD	225	mW

Electrical Characteristics (at TA = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V _{(BR)R}	30	-	-	V	I _R =100μA
Maximum Instantaneous Forward Voltage	V _F	-	-	500	mV	I _F =200mA
Maximum Average Reverse Current	I _R	-	-	50	μA	VR1=10V
		-	-	100	μA	VR2=30V

Notes: 1. Measured at 1.0 MHz and 0 reverse bias voltage.

2. ESD sensitive product handling required.

Characteristics Curve

FIG. 1 - FORWARD CHARACTERISTICS

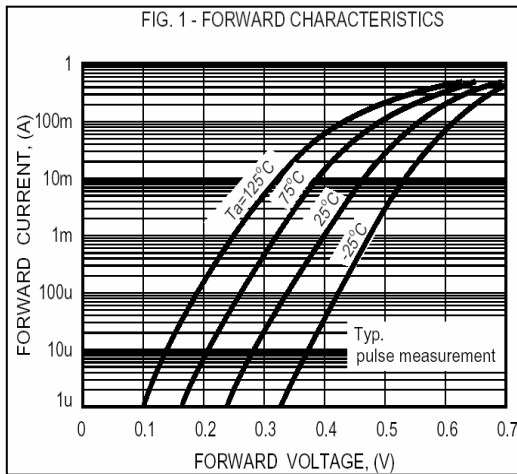


FIG. 2 - REVERSE CHARACTERISTICS

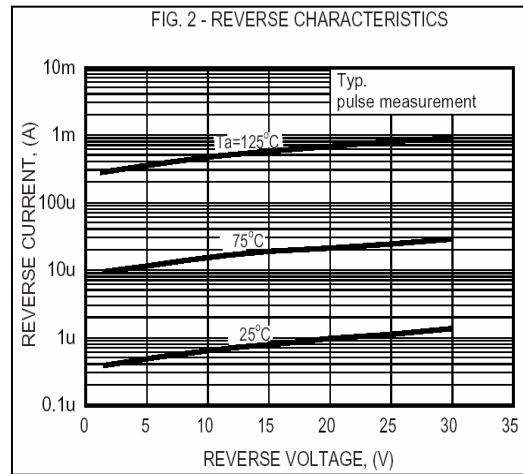


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

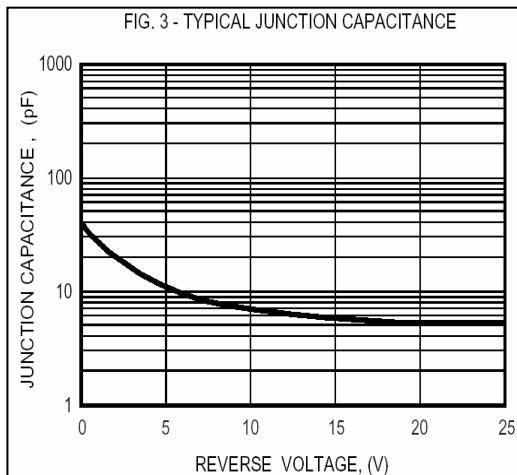
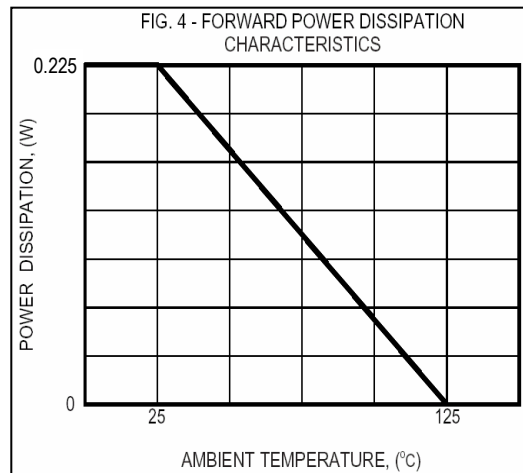


FIG. 4 - FORWARD POWER DISSIPATION CHARACTERISTICS

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